

TITLE: FLASH MEMORY CELL HAVING REDUCED LEAKAGE CURRENT INVENTOR(S): Sheung Hee Park, Richard M. Fastow, and Dong-Hyuk Ju USSN: 10/618,191 Attorney Docket #: AMD-H0534

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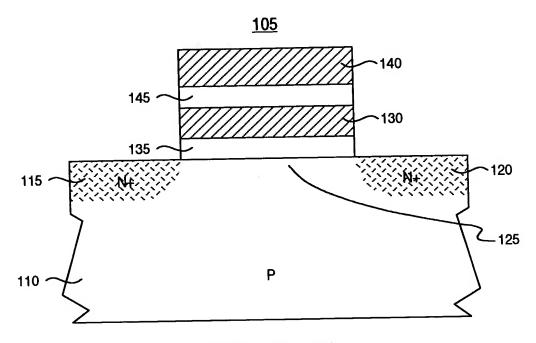


FIGURE 1A (CONVENTIONAL ART)

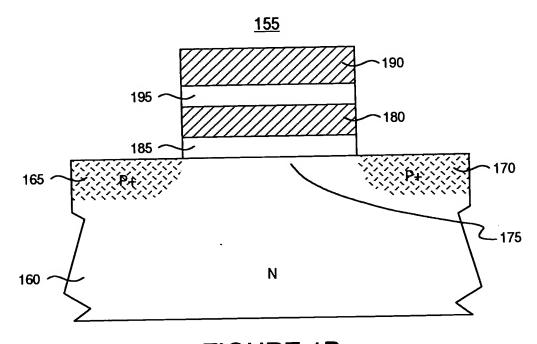


FIGURE 1B (CONVENTIONAL ART)

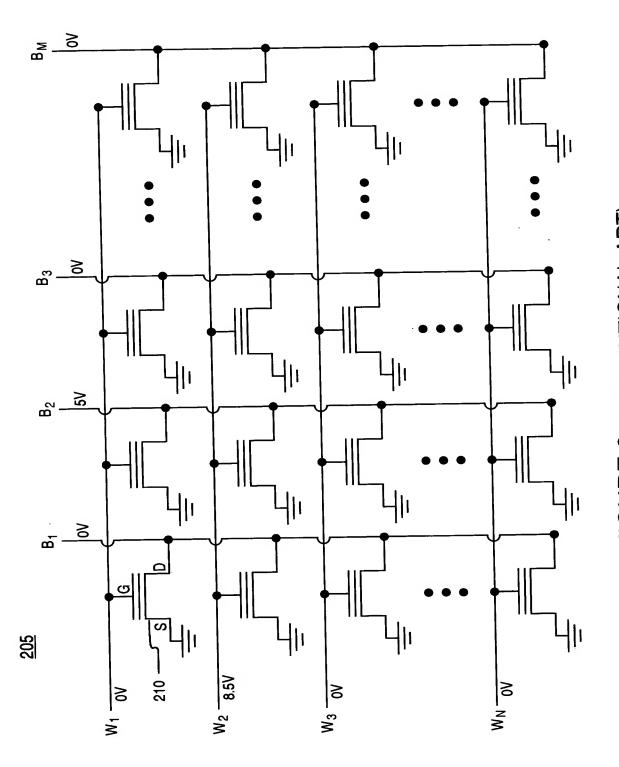


FIGURE 2 (CONVENTIONAL ART)

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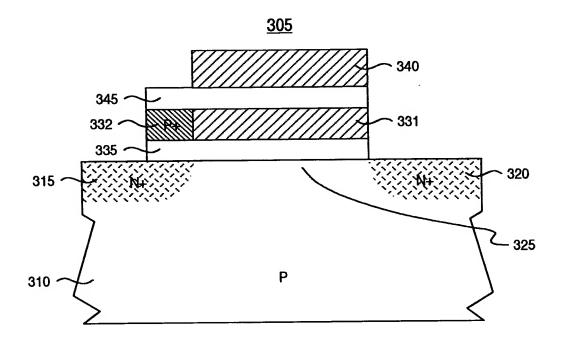


FIGURE 3

445 432 435 415 P

FIGURE 4

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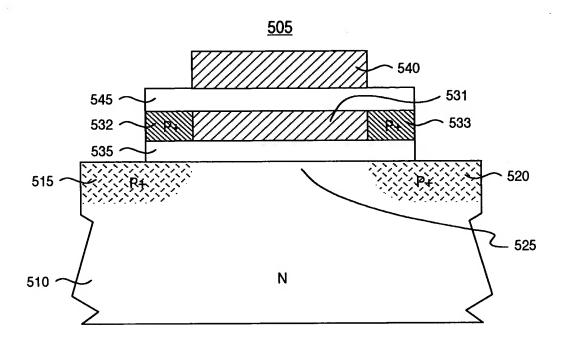


FIGURE 5

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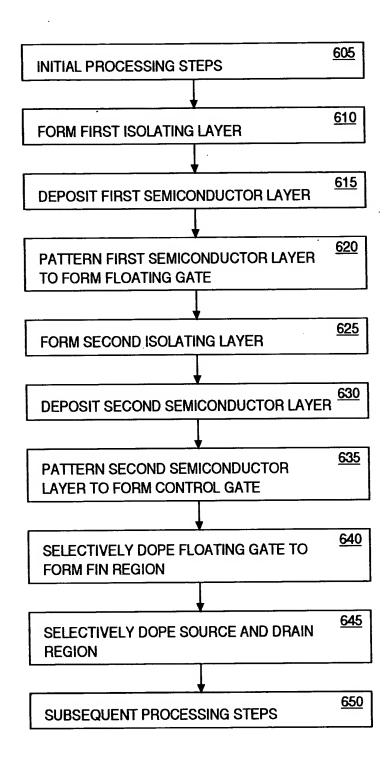


FIGURE 6